



### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C		
-12V	11.7m $\Omega$ @ V <sub>GS</sub> = -4.5V	-19A		
-12V	18.6mΩ @ $V_{GS} = -2.5V$	-15A		

### **Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Backlighting
- Power Management Functions
- DC-DC Converters

## **Features and Benefits**

- Low R<sub>DS(ON)</sub> Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products (PowerDI<sup>®</sup>)
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- ESD Protected Up To 3kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

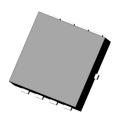
### **Mechanical Data**

- Case: PowerDI3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
   Terminals: Finish Matte Tin Annealed over Copper Leadframe.

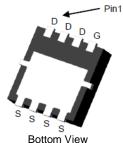
   Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.072grams (Approximate)

### PowerDI3333-8 (Type UX)

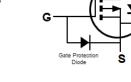








Pin Configuration



**Equivalent Circuit** 

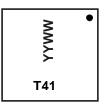
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMP1011LFV-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel
DMP1011LFV-13	PowerDI3333-8 (Type UX)	3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



T41 = Product Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 for 2017) WW = Week Code (01 to 53)



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V <sub>DSS</sub>	-12	V
Gate-Source Voltage			V <sub>GSS</sub>	- 6	V
Continuous Drain Current (Note C) // 45//	t<10s	$T_A = +25$ °C $T_A = +70$ °C	l <sub>D</sub>	-13 -10	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	l <sub>D</sub>	-19 -15	А
Maximum Continuous Body Diode Forward Current (Note 6)			I <sub>S</sub>	3	Α
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	70	Α
Avalanche Current (Note 7) L = 0.3mH			I <sub>AS</sub>	24	А
Avalanche Energy (Note 7) L = 0.3mH			Eas	86	mJ

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		$P_{D}$	1.05	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	118	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	83.5	
Total Power Dissipation (Note 6)		$P_{D}$	2.16	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	5	57	
Themal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	40.3	°C/W
Thermal Resistance, Junction to Case (Note 6)		R <sub>0</sub> JC	11.7	
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

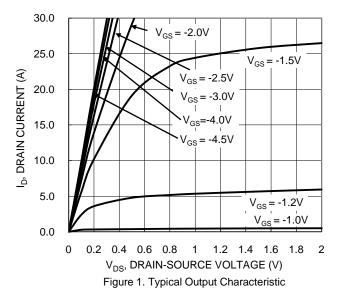
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	$BV_{DSS}$	-12	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current (T <sub>J</sub> = +25°C)	I <sub>DSS</sub>	1	_	-1	μA	$V_{DS} = -9.6V, V_{GS} = 0V$	
Gate-Source Leakage		_	_	-100	nA	$V_{GS} = -6V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.6	_	-1.2	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	RDS(ON)	1	9.8	11.7	mΩ	$V_{GS} = -4.5V$ , $I_{D} = -12A$	
Static Drain-Source Off-Resistance	KDS(ON)	1	14.6	18.6		$V_{GS} = -2.5V, I_{D} = -9A$	
Diode Forward Voltage	$V_{SD}$	1	-0.8	-1.0	V	$V_{GS} = 0V, I_{S} = -16A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	-	913	_		$V_{DS} = -6V, V_{GS} = 0V,$ f = 1.0MHz	
Output Capacitance	Coss		458		pF		
Reverse Transfer Capacitance	$C_{rss}$		53	_			
Gate Resistance	$R_g$	_	1.85	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = -6V)	$Q_g$	1	9.5	_			
Total Gate Charge (V <sub>GS</sub> = -4.5V)	$Q_g$		7.1	_	nC	Vps = -6V. Ip = -12A	
Gate-Source Charge	$Q_{gs}$	_	1.4	_	IIC	V <sub>DS</sub> = -0V, I <sub>D</sub> = -12A	
Gate-Drain Charge	$Q_{gd}$	_	1.1	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	6.3	_		$V_{DS} = -6V, V_{GS} = -4.5V,$ $R_L = 1\Omega, R_g = 4.7\Omega, I_D = -12A$	
Turn-On Rise Time	t <sub>R</sub>	_	2.6	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	14.4	_	ns		
Turn-Off Fall Time	t <sub>F</sub>		3.9	_		-	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	13.5	_	ns	I <sub>F</sub> = -12A, dI/dt = 100A/μs	
Body Diode Reverse Recovery Charge	$Q_{RR}$	_	2.5	_	nC	I <sub>F</sub> = -12A, dl/dt = 100A/µs	

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 7. IAs and EAs ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
   8. Short duration pulse test used to minimize self-heating effect.
   9. Guaranteed by design. Not subject to production testing.





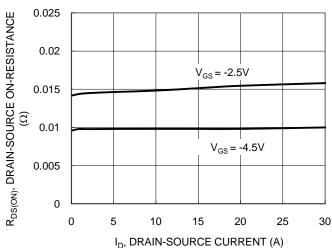


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

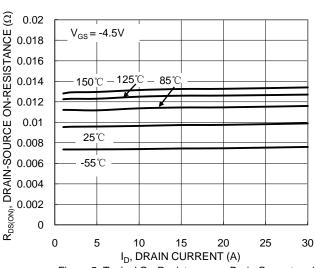


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

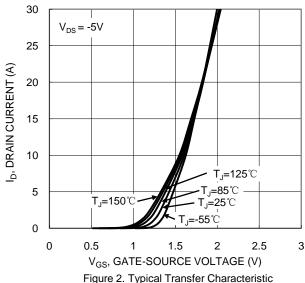


Figure 2. Typical Transfer Characteristic

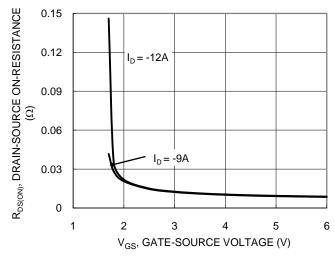


Figure 4. Typical Transfer Characteristic

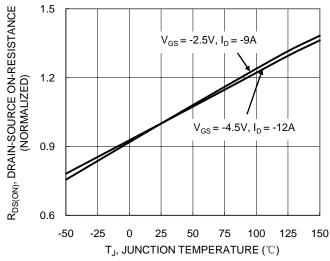


Figure 6. On-Resistance Variation with Temperature



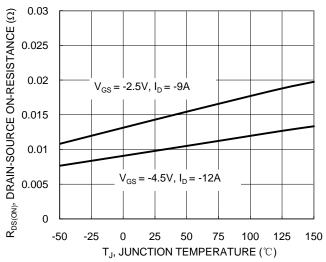


Figure 7. On-Resistance Variation with Temperature

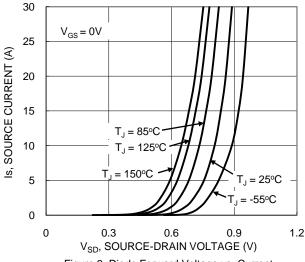
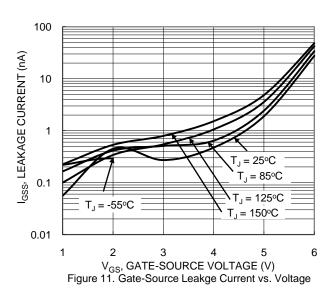
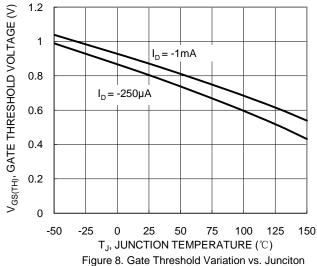


Figure 9. Diode Forward Voltage vs. Current





Temperature

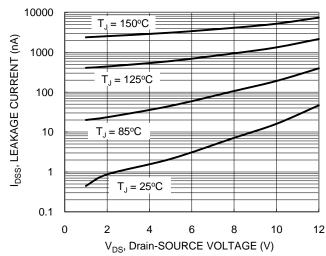
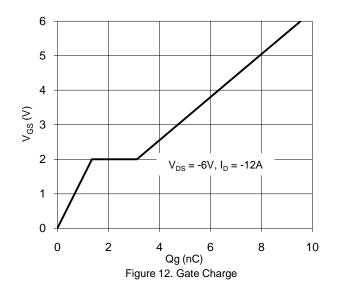
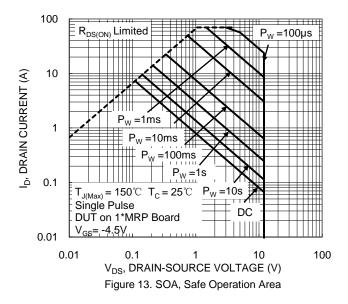
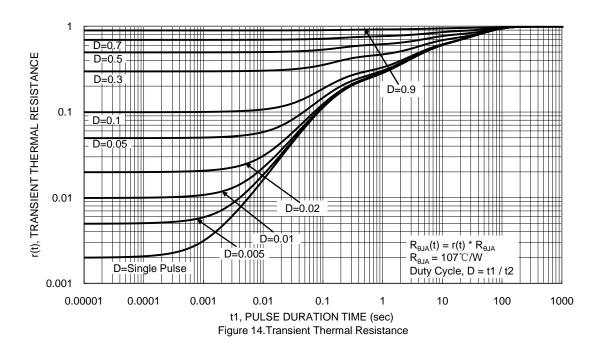


Figure 10. Typical Drain-Source Leakge Current vs. Voltage







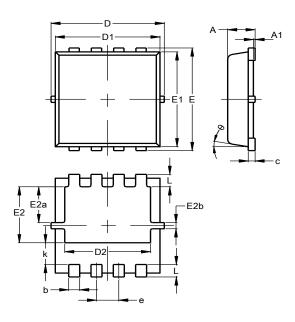




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (Type UX)

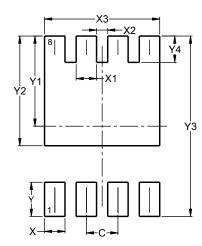


PowerDI3333-8 (Type UX)					
Dim	Min	Тур			
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
C	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E2a	0.95	1.35	1.15		
E2b	0.10	0.30	0.20		
е	0.65 BSC				
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (Type UX)



Dimensions	value (in mm)			
С	0.650			
X	0.420			
X1	0.420			
X2	0.230			
Х3	2.370			
Υ	0.700			
Y1	1.850			
Y2	2.250			
Y3	3.700			
Y4	0.540			



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